

N-Channel RF Amplifier J211, MMBFJ211

Description

This device is designed for HF/VHF mixer/amplifier and applications where process 50 is not adequate. Sufficient gain and low–noise for sensitive receivers. Sourced from process 90.

MAXIMUM RATINGS ($T_A = 25^{\circ}C$ unless otherwise noted) (Notes 1, 2)

Symbol	Parameter	Value	Unit
V_{DG}	Drain-Gate Voltage	25	V
V _{GS}	Gate-Source Voltage	-25	V
I_{GF}	Forward Gate Current	10	mA
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. These ratings are based on a maximum junction temperature of 150°C.
- These are steady-state limits. onsemi should be consulted on applications involving pulsed or low- duty-cycle operations.

THERMAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

		M		
Symbol	Parameter	J211 (Note 3)	MMBFJ211 (Note 3)	Unit
P _D	Total Device Dissipation	350	225	mW
	Derate Above 25°C	2.8	1.8	mW/°C
$R_{ heta JC}$	Thermal Resistance, Junction-to-Case	125	-	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	357	556	°C/W

Device mounted on FR-4 PCB 36 mm x 18 mm x 1.5 mm; mounting pad for the collector lead minimum 6 cm².



- 1. Drain
- 2. Source
- 3. Gate

Bent Lead Tape & Reel Ammo Packing

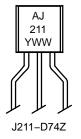
> TO-92 3 CASE 135AR

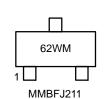


NOTE: Source & Drain are interchangeable

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MARKING DIAGRAM





J211, 62W = Device Code
A = Assembly Site
WW = Work Week Number
Y = Year of Production
M = Date Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Max	Unit	
OFF CHARACTERISTICS						
V _{(BR)GSS}	Gate-Source Breakdown Voltage	$I_G = 1.0 \mu A, V_{DS} = 0$	-25	-	V	
I _{GSS}	Gate Reverse Current	V _{GS} = 15 V, V _{DS} = 0	-	-100	рА	
V _{GS} (off)	Gate-Source Cut-Off Voltage	V _{DS} = 15 V, I _D = 1.0 nA	-2.5	-4.5	V	
ON CHARACTERISTICS						
I _{DSS}	Zero-Gate Voltage Drain Current (Note 4)	V _{DS} = 15 V, V _{GS} = 0	7.0	20	mA	
SMALL SIGNAL CHARACTERISTICS						
9fs	Common Source Forward Transconductance	$V_{DS} = 15 \text{ V}, V_{GS} = 0, f = 1.0 \text{ kHz}$	7000	12000	μmhos	
goss	Common Source Output Conductance	$V_{DS} = 15 \text{ V}, V_{GS} = 0, f = 1.0 \text{ kHz}$	-	200	μmhos	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse test: pulse width $\leq 300 \, \mu s$

TYPICAL PERFORMANCE CHARACTERISTICS

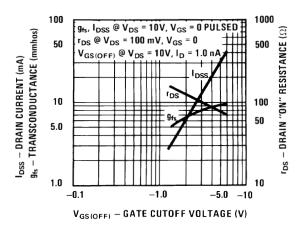


Figure 1. Parameter Interactions

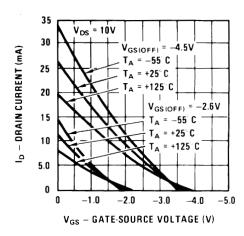


Figure 3. Transfer Characteristics

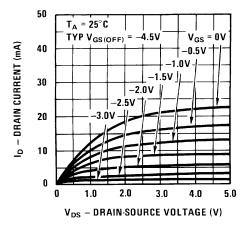


Figure 2. Common Drain-Source

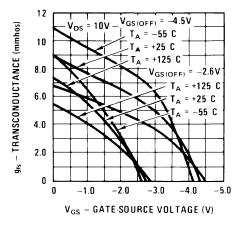


Figure 4. Transfer Characteristics

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

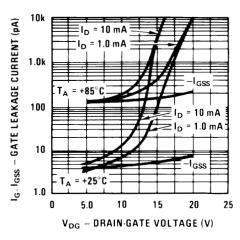


Figure 5. Leakage Current vs. Voltage

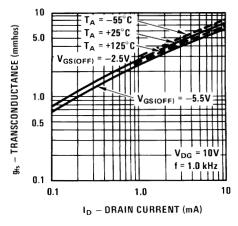


Figure 7. Transconductance vs. Drain Current

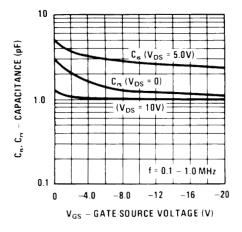


Figure 9. Capacitance vs. Voltage

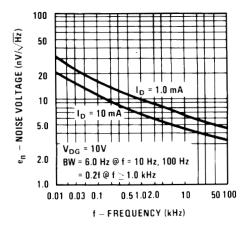


Figure 6. Noise Voltage vs. Frequency

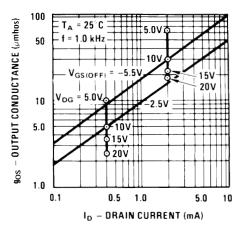


Figure 8. Output Conductance vs. Drain Current

COMMON SOURCE CHARACTERISTICS

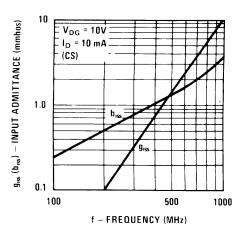


Figure 10. Input Admittance

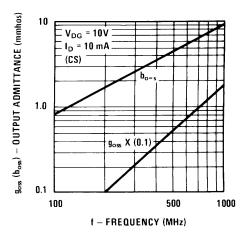


Figure 12. Output Admittance

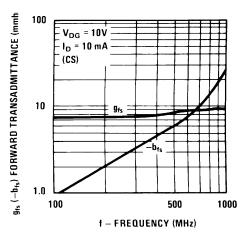


Figure 11. Forward Transadmittance

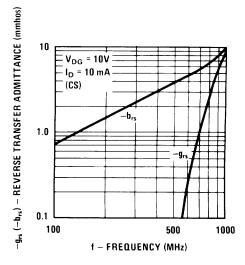


Figure 13. Reverse Transadmittance

J211, MMBFJ211

COMMON GATE CHARACTERISTICS

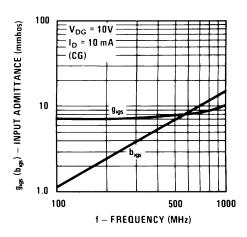


Figure 14. Input Admittance

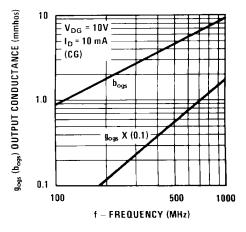


Figure 16. Output Admittance

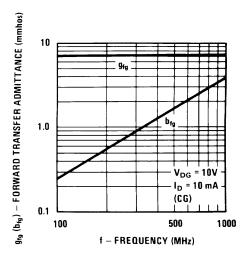


Figure 15. Forward Transadmittance

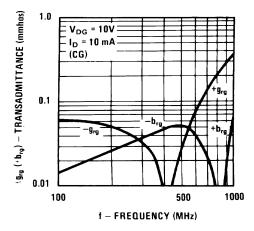


Figure 17. Reverse Transadmittance

ORDERING INFORMATION

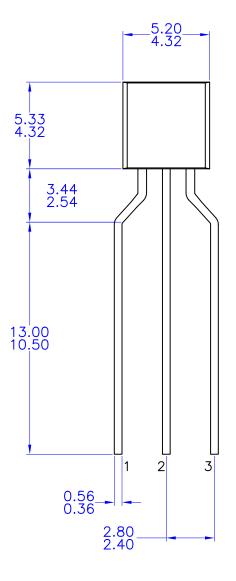
Part Number	Top Mark	Package	Packing Method [†]
J211-D74Z	J211	TO-92 3L (Pb-Free)	Ammo
MMBFJ211	62W	SOT-23 3L (Pb-Free)	Tape and Reel

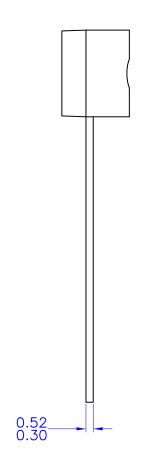
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TO-92 3 4.83x4.76 LEADFORMED

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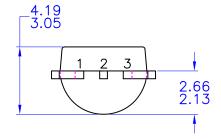
DATE 30 SEP 2016





NOTES: UNLESS OTHERWISE SPECIFIED

- A) DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DRAWING CONFORMS TO ASME Y14.5M-1994



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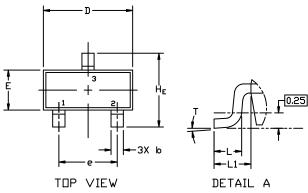




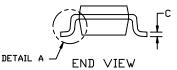
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DATE 01 MAR 2023









NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		INCHES			
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Ε	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10°	0*		10°

GENERIC MARKING DIAGRAM*

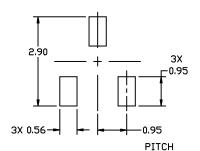


XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

STYLES ON PAGE 2

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MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



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STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	N	
STYLE 9:	STYLE 10:	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN		PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE		2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE		3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	N PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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